Czochralski 単結晶成長法を用いた気固相界面での相互作用による
SiC、SiO2 凝結過程の数値解析

Numerical analysis of SiC and SiO2 deposition processes by gas-solid interaction in
Czochralski silicon crystal growth

九大応力研 刘鑫, 高冰, 中野智, 原田博文, 宮村佳児, 柿本浩一
RIAM, Kyushu Univ.

Xin Liu, Bing Gao, Satoshi Nakano, Hirofumi Harada, Yoshiji Miyamura and Koichi Kakimoto
E-mail: liuxin@riam.kyushu-u.ac.jp

Czochralski (CZ) crystal growth of single crystalline silicon (Si) is invariably accompanied by
transport of species such as carbon (C), oxygen (O), and related products from chemical reactions in the
high temperature range. Complex reactions among species and furnace elements result in the formation of
different deposition layers. Depositions of Si, SiO, SiO2 and SiC in CZ-Si system are undesirable owing to
their negative effects on the crystal growth process, such as poly Si growth, degradation of heater and
obstruction of gas flow. Therefore, mechanisms of the gas-solid interaction and the deposition process are
critical for the active control of impurity transport in CZ-Si crystal growth.

To investigate the dynamic deposition processes, transient global simulations of heat and mass
transport were conducted for melting process of CZ-Si crystal growth. The deposition processes of SiO2
and SiC are shown schematically in Fig. 1. An extended chemical model, which accounts for the gas-solid
interactions, was developed to predict the deposition rate of SiO2 and SiC on furnace elements. The
thickness of deposition layers could also be estimated by the integration of the deposition rate for the
duration of the melting process. Thicknesses of SiC deposition layers along the inner and outer surfaces of
the heater are present in Fig.2, as well as the temperature profiles. The SiC deposition on the inner side of
the heater is remarkable due to the SiO absorption by graphite. The removal of SiO must be reinforced to
reduce the deposits of SiO2 and SiC by the enhancement of gas flow in CZ-Si crystal growth.

Fig. 1 Depositions of SiO2 and SiC in hot zone

Fig. 2 Deposition layer of SiC on the heater

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